

Features

- Dual USB port power switches
- Over-current and thermal protection
- 1.5A accurate current limiting
- Reverse Current Blocking
- 115mΩ on-resistance
- Input voltage range: 2.7V – 5.5V
- 0.6ms typical rise time
- Very low shutdown current: 1uA (max)
- Fault report (FLG) with blanking time (7ms typ)
- ESD protection: 4.5KV HBM, 350V MM
- Active high (AP2172) or active low (AP2162) enable
- Ambient temperature range -40°C to 85°C
- SOP-8L and MSOP-8L-EP (Exposed Pad): Available in "Green" Molding Compound (No Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)
- UL Recognized, File Number E322375
- IEC60950-1 CB Scheme Certified

Description

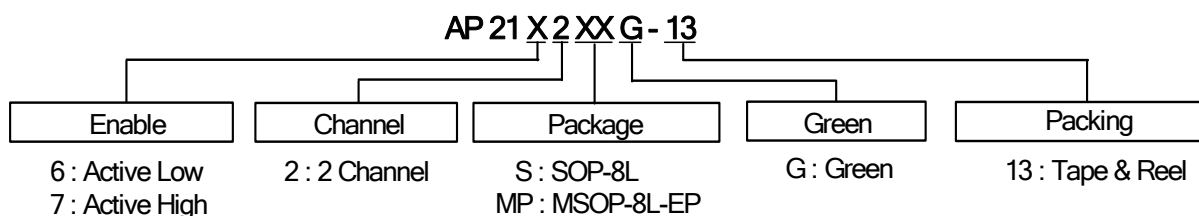
The AP2162 and AP2172 are integrated high-side power switches optimized for Universal Serial Bus (USB) and other hot-swap applications. The family of devices complies with USB 2.0 and available with both polarities of Enable input. They offer current and thermal limiting and short circuit protection as well as controlled rise time and under-voltage lockout functionality. A 7ms deglitch capability on the open-drain Flag output prevents false over-current reporting and does not require any external components.

All devices are available in SOP-8L and MSOP-8L-EP packages.

Applications

- Consumer electronics – LCD TV & Monitor, Game Machines
- Communications – Set-Top-Box, GPS, Smartphone
- Computing – Laptop, Desktop, Servers, Printers, Docking Station, HUB

Ordering Information

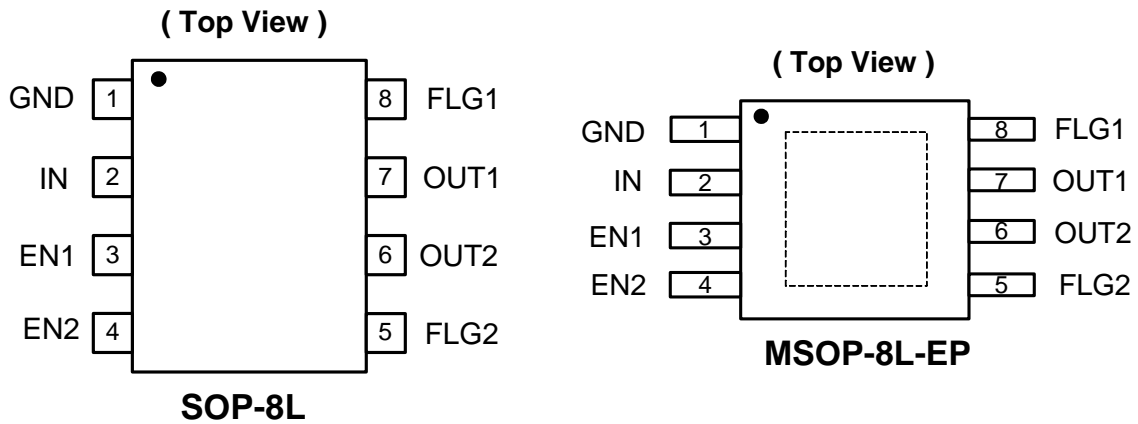


Device	Package Code	Packaging (Note 2)	13" Tape and Reel	
			Quantity	Part Number Suffix
AP21X2SG-13	S	SOP-8L	2500/Tape & Reel	-13
AP21X2MPG-13	MP	MSOP-8L-EP	2500/Tape & Reel	-13

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

2. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

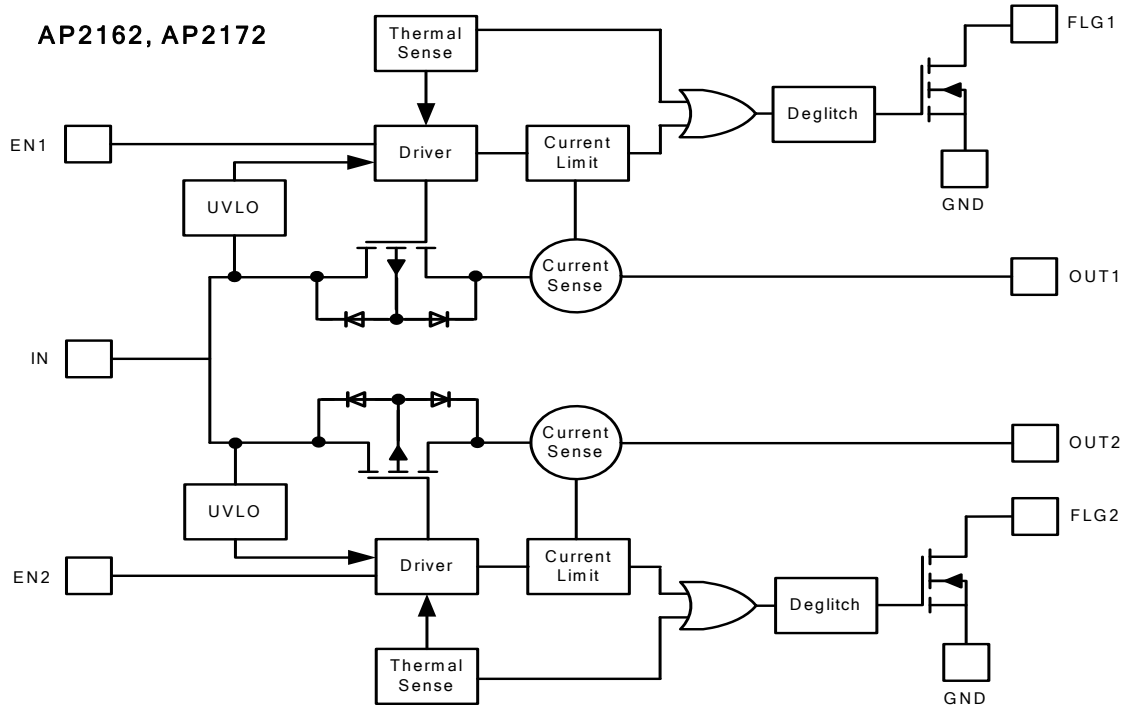
Pin Assignment



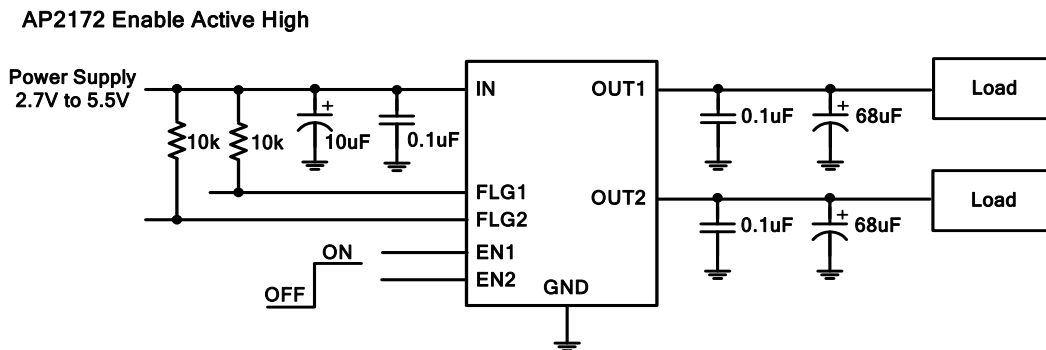
Pin Descriptions

Pin Name	Pin Number	Descriptions
GND	1	Ground
IN	2	Voltage input pin
EN1	3	Switch 1 enable input, active low (AP2162) or active high (AP2172)
EN2	4	Switch 2 enable input, active low (AP2162) or active high (AP2172)
FLG2	5	Switch 2 over-current and over-temperature fault report; open-drain flag is active low when triggered
OUT2	6	Switch 2 voltage output pin
OUT1	7	Switch 1 voltage output pin
FLG1	8	Switch 1 over-current and over-temperature fault report; open-drain flag is active low when triggered

Functional Block Diagram



Typical Application Circuit



Available Options

Part Number	Channel	Enable Pin (EN)	Current Limit (Typical)	Recommended Maximum Continuous Load Current
AP2162	2	Active Low	1.5A	1.0A
AP2172	2	Active High	1.5A	1.0A

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Units
ESD HBM	Human Body Model ESD Protection	3	KV
ESD MM	Machine Model ESD Protection	300	V
V_{IN}	Input Voltage	6.5	V
V_{OUT}	Output Voltage	$V_{IN} + 0.3$	V
V_{EN}, V_{FLG}	Enable Voltage	6.5	V
I_{load}	Maximum Continuous Load Current	Internal Limited	A
T_{Jmax}	Maximum Junction Temperature	150	°C
T_{ST}	Storage Temperature Range (Note 3)	-65 to 150	°C

Notes: 3. UL Recognized Rating from -30°C to 70°C (Diodes qualified T_{ST} from -65°C to 150°C)

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V_{IN}	Input voltage	2.7	5.5	V
I_{OUT}	Output Current	0	1.0	A
T_A	Operating Ambient Temperature	-40	85	°C

Electrical Characteristics

($T_A = 25^\circ\text{C}$, $V_{IN} = +5.0\text{V}$, unless otherwise stated)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
V_{UVLO}	Input UVLO	$R_{load} = 1\text{k}\Omega$	1.6	1.9	2.5	V
I_{SHDN}	Input Shutdown Current	Disabled, $I_{OUT} = 0$		0.5	1	μA
I_Q	Input Quiescent Current, Dual	Enabled, $I_{OUT} = 0$		100	160	μA
I_{LEAK}	Input Leakage Current	Disabled, OUT grounded			1	μA
I_{REV}	Reverse Leakage Current	Disabled, $V_{IN} = 0\text{V}$, $V_{OUT} = 5\text{V}$, I_{REV} at V_{IN}		1		μA
$R_{DS(ON)}$	Switch on-resistance	$V_{IN} = 5\text{V}$, $I_{OUT} = 0.5\text{A}$, $-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$		115	150	$\text{m}\Omega$
		MSOP-8L-EP		120	160	$\text{m}\Omega$
		SOP-8L		140	180	$\text{m}\Omega$
I_{SHORT}	Short-circuit current limit	Enabled into short circuit, $C_L = 68\mu\text{F}$		1.4		A
I_{LIMIT}	Over-Load Current Limit	$V_{IN} = 5\text{V}$, $V_{OUT} = 4.6\text{V}$, $C_L = 68\mu\text{F}$, $-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$	1.1	1.5	1.9	A
I_{Trig}	Current limiting trigger threshold	$V_{IN} = V_{EN}$, Output Current Slew rate ($< 100\text{A/s}$), $C_L = 68\mu\text{F}$		2.4		A
V_{IL}	EN Input Logic Low Voltage	$V_{IN} = 2.7\text{V}$ to 5.5V			0.8	V
V_{IH}	EN Input Logic High Voltage	$V_{IN} = 2.7\text{V}$ to 5.5V	2			V
I_{SINK}	EN Input leakage	$V_{EN} = 5\text{V}$			1	μA
$T_{D(ON)}$	Output turn-on delay time	$C_L = 1\mu\text{F}$, $R_{load} = 10\Omega$		0.05		ms
T_R	Output turn-on rise time	$C_L = 1\mu\text{F}$, $R_{load} = 10\Omega$		0.6	1.5	ms
$T_{D(OFF)}$	Output turn-off delay time	$C_L = 1\mu\text{F}$, $R_{load} = 10\Omega$		0.01		ms
T_F	Output turn-off fall time	$C_L = 1\mu\text{F}$, $R_{load} = 10\Omega$		0.05	0.1	ms
R_{FLG}	FLG output FET on-resistance	$I_{FLG} = 10\text{mA}$		30	50	Ω
T_{Blank}	FLG blanking time	$C_{IN} = 10\mu\text{F}$, $C_L = 68\mu\text{F}$	4	7	15	ms
T_{SHDN}	Thermal shutdown threshold	Enabled, $R_{load} = 1\text{k}\Omega$		140		$^\circ\text{C}$
T_{HYS}	Thermal shutdown hysteresis			25		$^\circ\text{C}$
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOP-8L (Note 4)		110		$^\circ\text{C/W}$
		MSOP-8L-EP (Note 5)		60		$^\circ\text{C/W}$

- Notes:
4. Test condition for SOP-8L: Device mounted on FR-4 2-layer board, 2oz copper, with minimum recommended pad layout.
 5. Test condition for MSOP-8L-EP: Device mounted on FR-4 2-layer board, 2oz copper, with minimum recommended pad on top layer and 3 vias to bottom layer ground plane.

Typical Performance Characteristics

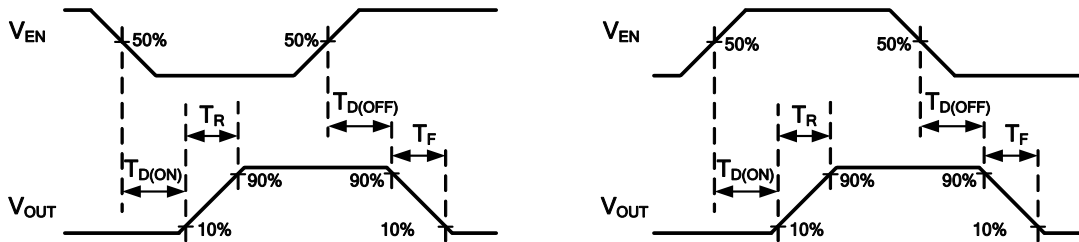
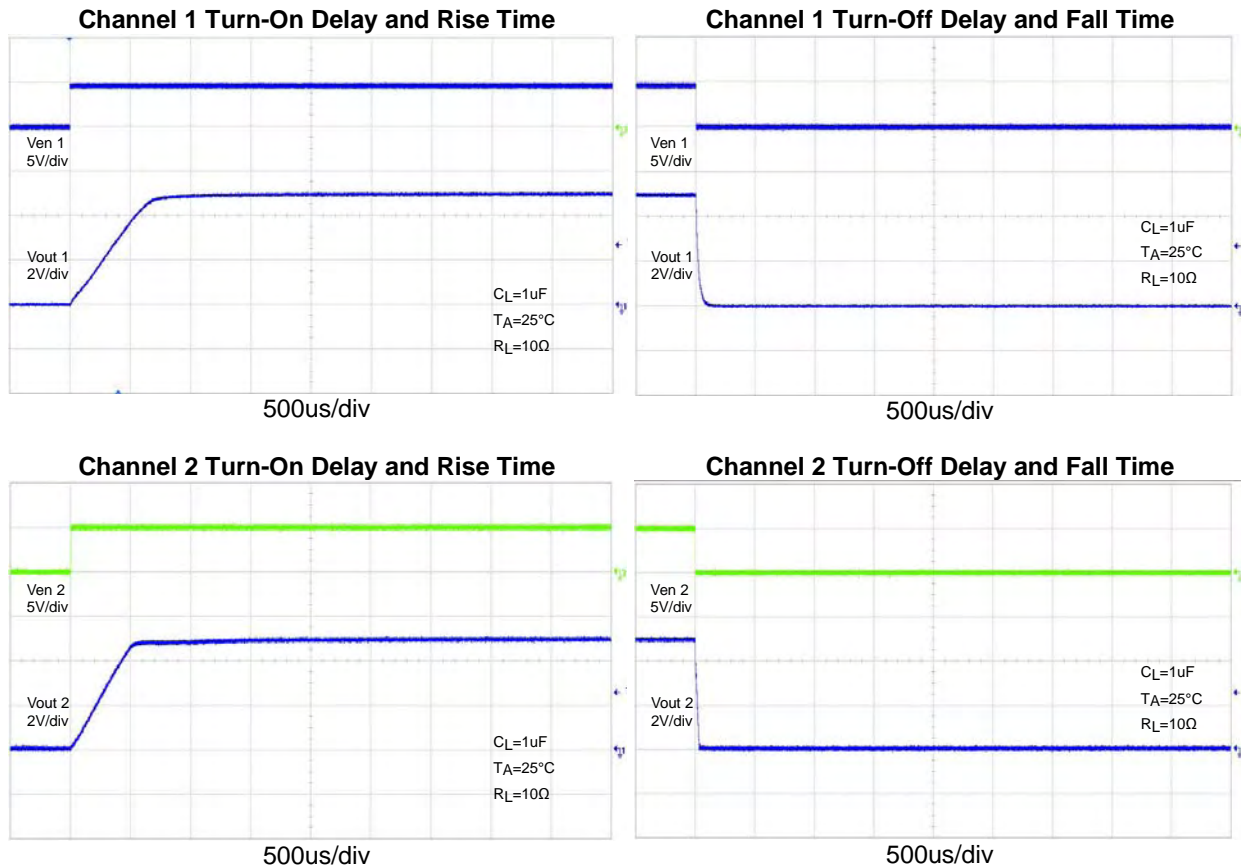
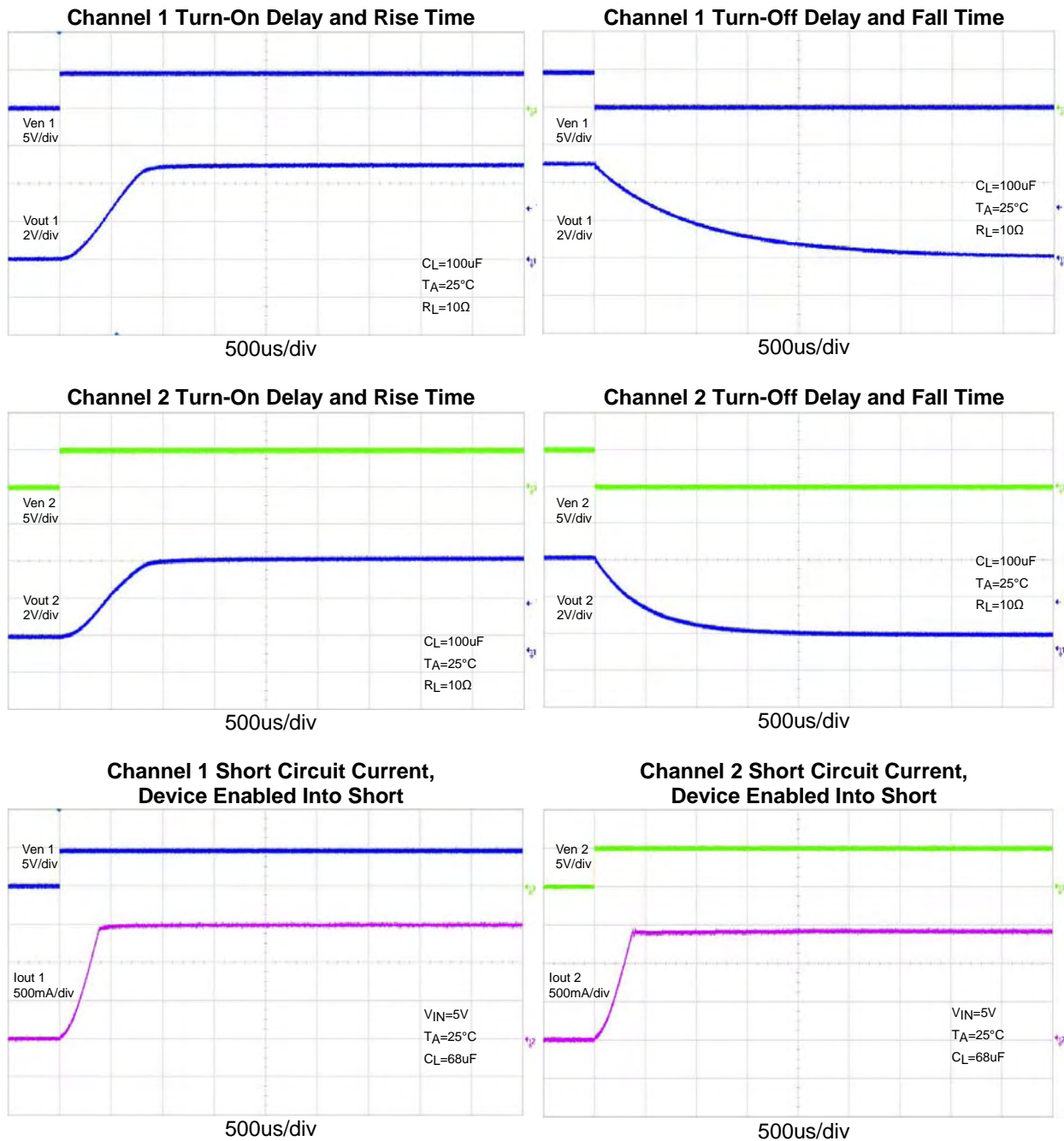


Figure 1. Voltage Waveforms: AP2162 (left), AP2172 (right)

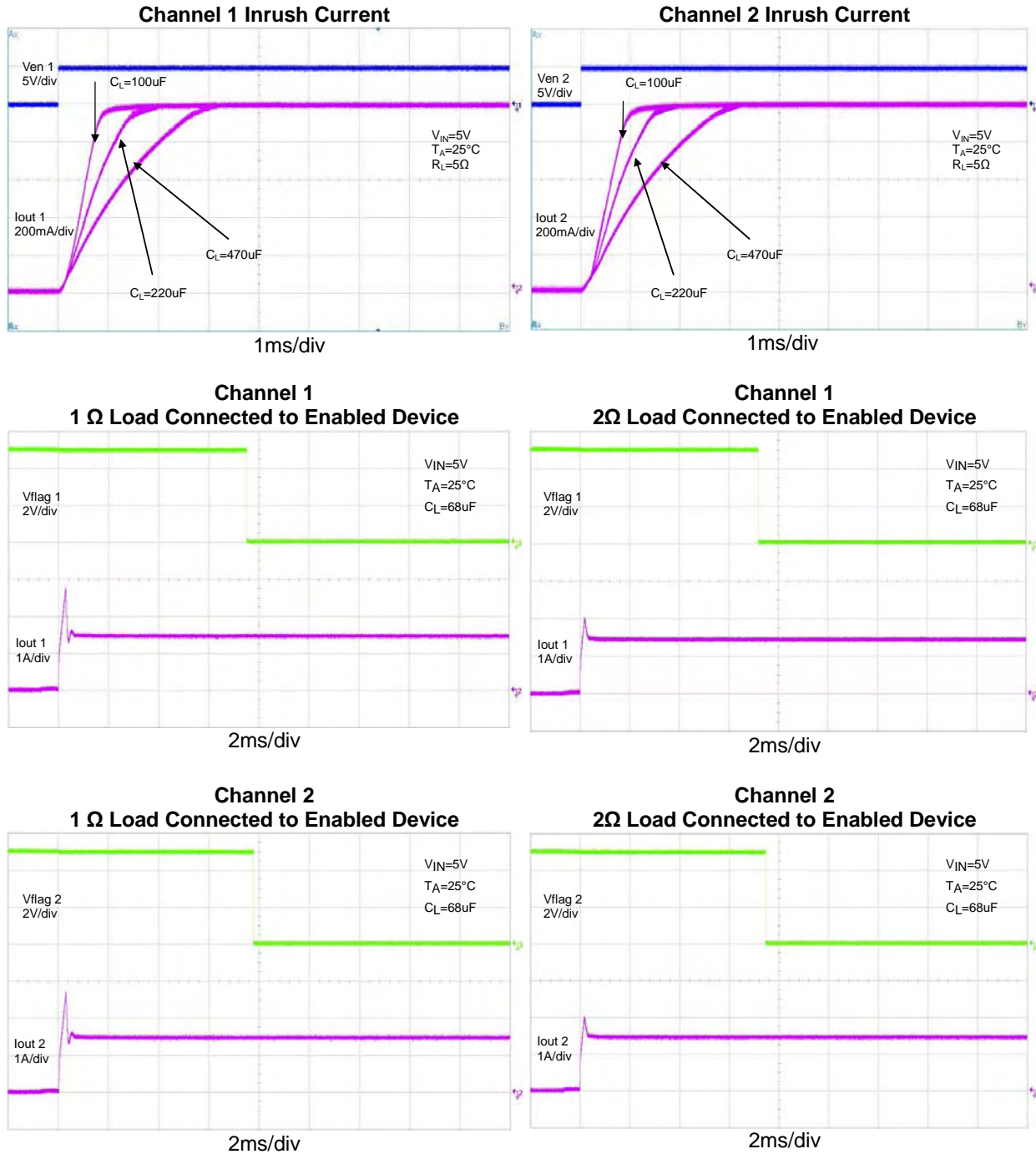
All Enable Plots are for AP2172 Active High



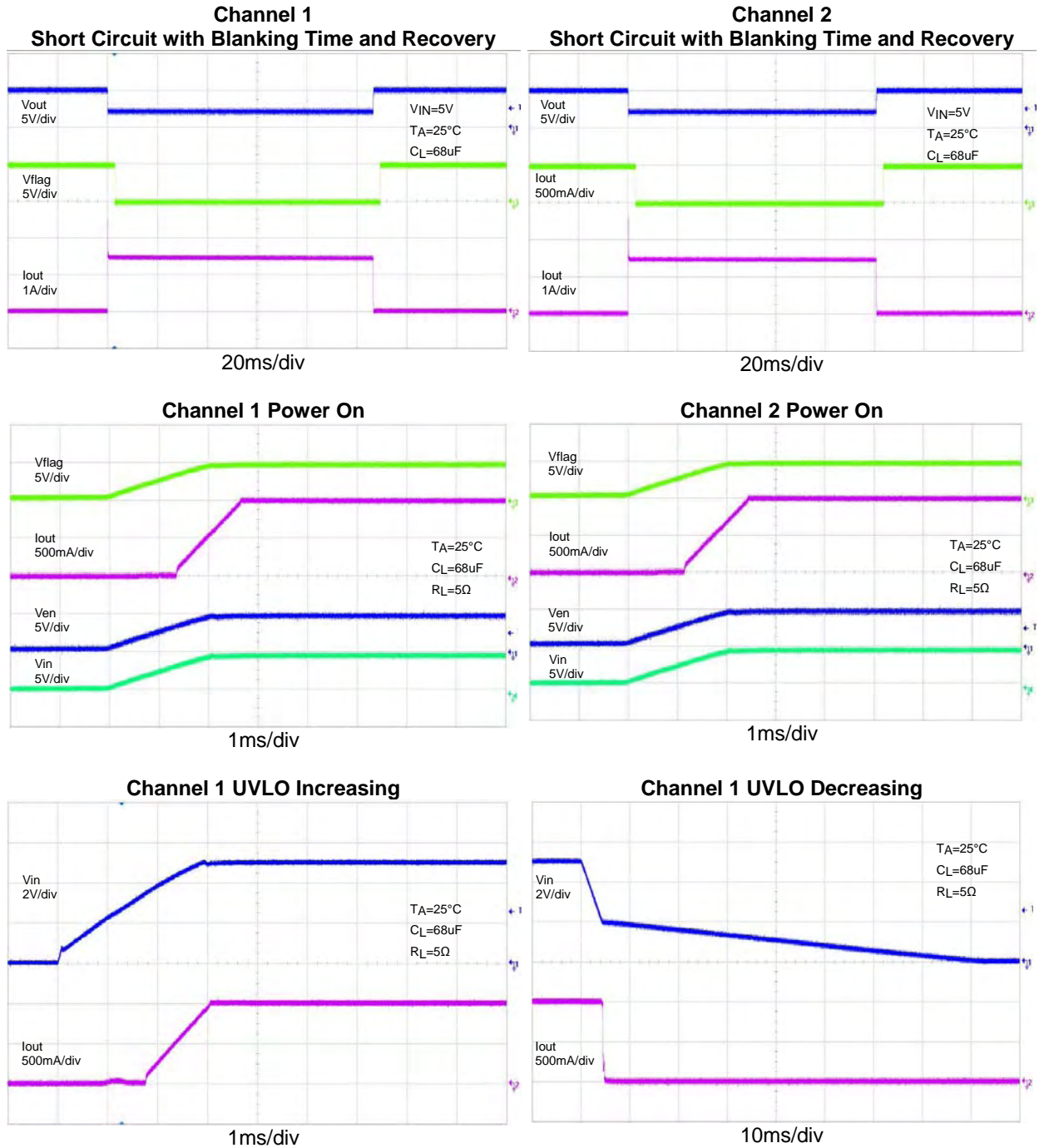
Typical Performance Characteristics (Continued)



Typical Performance Characteristics (Continued)

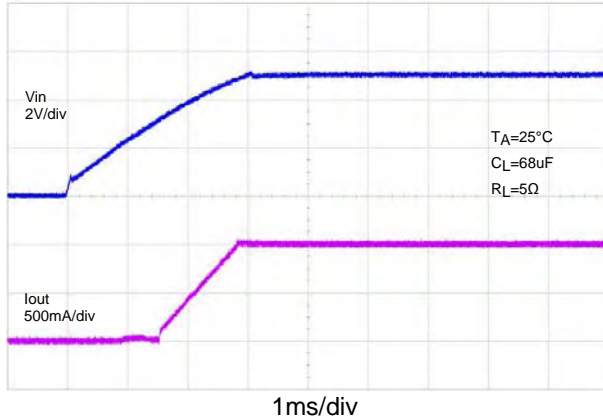


Typical Performance Characteristics (Continued)

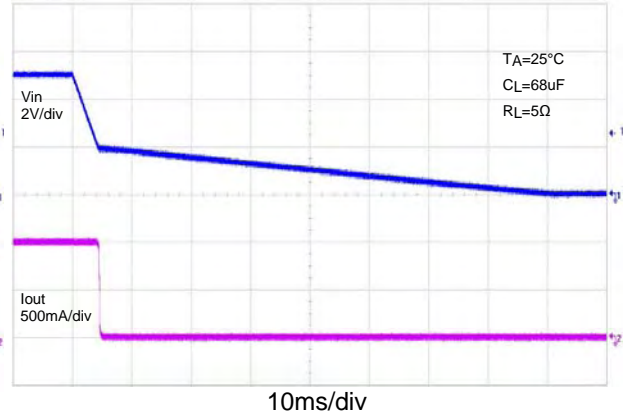


Typical Performance Characteristics (Continued)

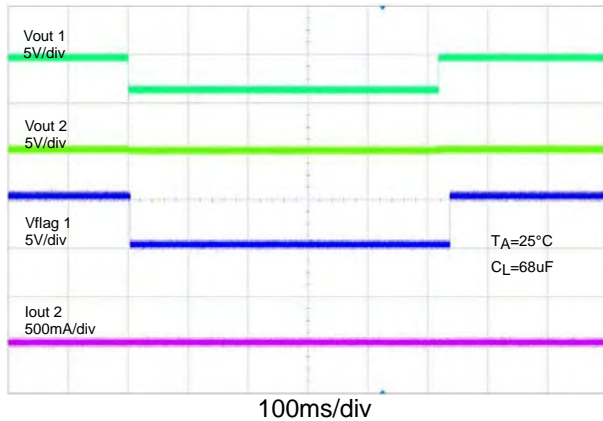
Channel 2 UVLO Increasing



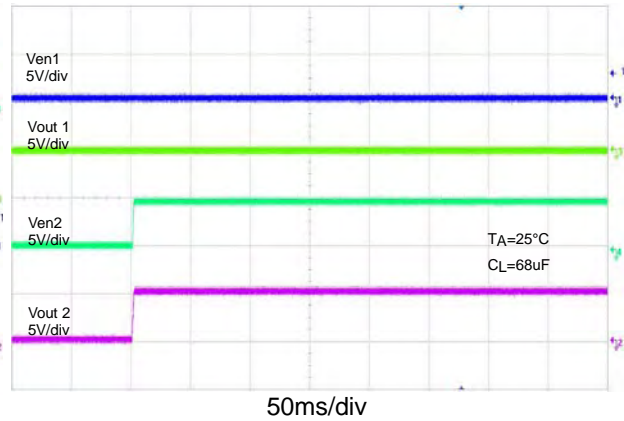
Channel 2 UVLO Decreasing



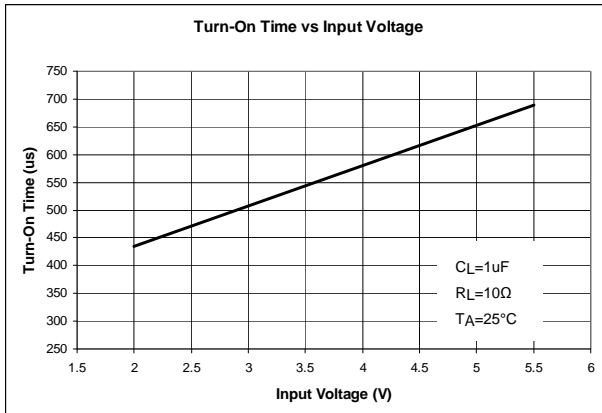
Channel 1 Enabled and Shorted with Channel 2 Disabled



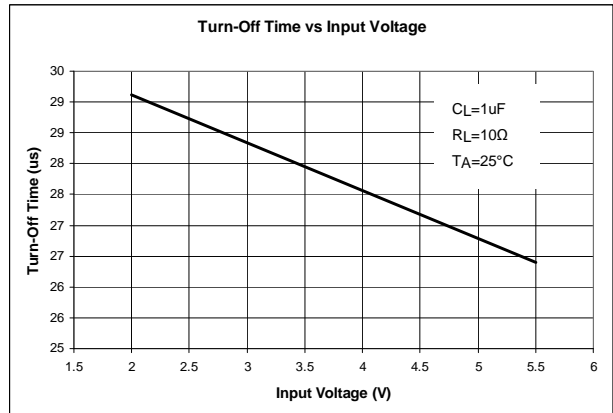
Channel 1 Disabled and Channel 2 Enabled



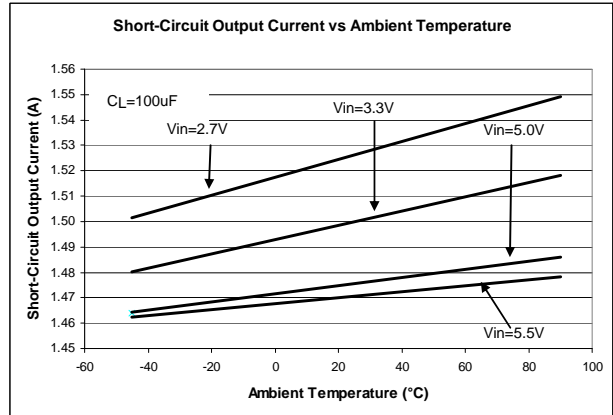
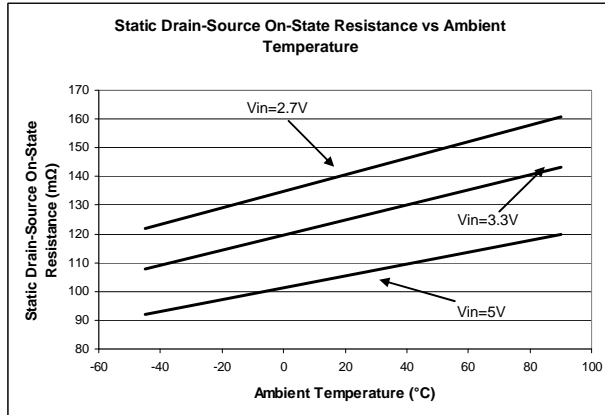
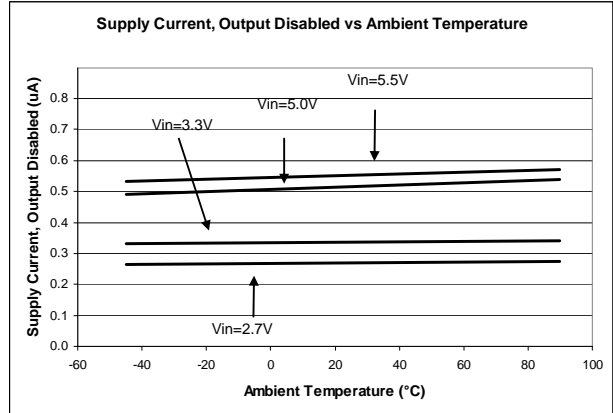
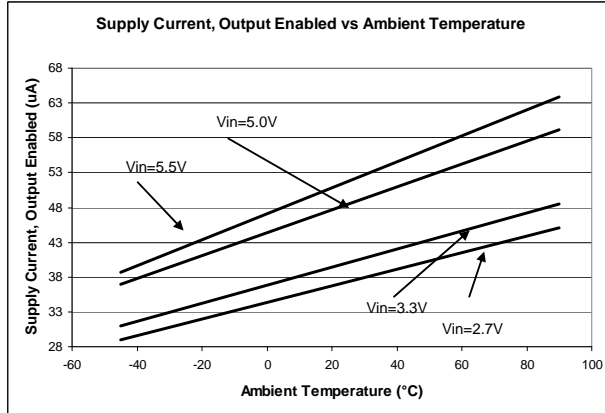
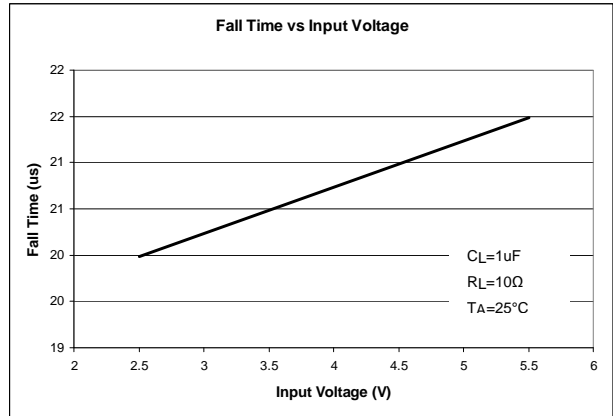
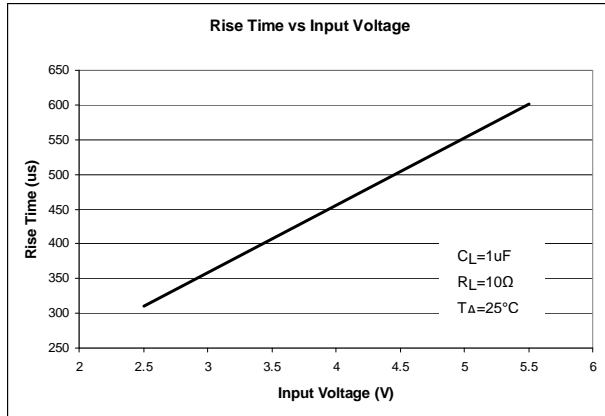
Turn-On Time vs Input Voltage



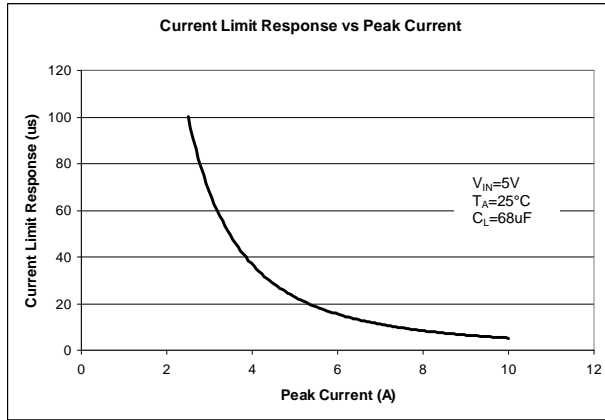
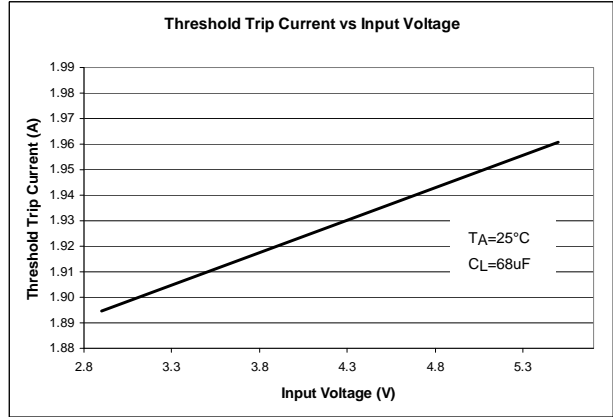
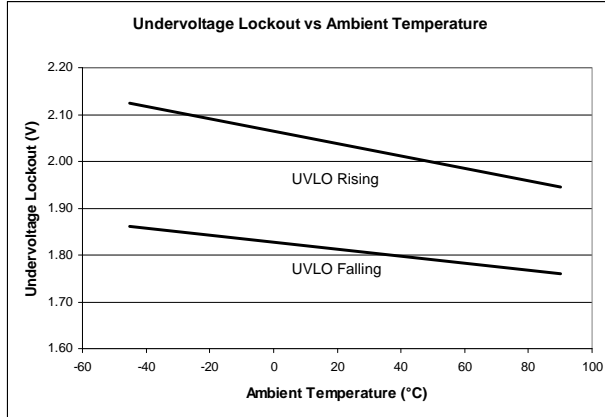
Turn-Off Time vs Input Voltage



Typical Performance Characteristics (Continued)



Typical Performance Characteristics (Continued)



Application Note

Power Supply Considerations

A 0.01- μ F to 0.1- μ F X7R or X5R ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the input and output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01- μ F to 0.1- μ F ceramic capacitor improves the immunity of the device to short-circuit transients.

Over-current and Short Circuit Protection

An internal sensing FET is employed to check for over-current conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted to GND before the device is enabled or before V_{IN} has been applied. The AP2162/AP2172 senses the short circuit and immediately clamps output current to a certain safe level namely I_{LIMIT} .

In the second condition, an output short or an overload occurs while the device is enabled. At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped (reached the over-current trip threshold), the device switches into current limiting mode and the current is clamped at I_{LIMIT} .

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold (I_{TRIG}) is reached or until the thermal limit of the device is exceeded. The AP2162/AP2172 is capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its current limiting mode and is set at I_{LIMIT} .

FLG Response

When an over-current or over-temperature shutdown condition is encountered, the FLG open-drain output goes active low after a nominal 7-ms deglitch timeout. The FLG output remains low until both over-current and over-temperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary over-current condition, which does not trigger the FLG due to the 7-ms deglitch timeout. The AP2162/AP2172 is designed to eliminate false over-current reporting without the need of external components to remove unwanted pulses.

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large current. Using the maximum operating ambient temperature (T_A) and $R_{DS(ON)}$, the power dissipation can be calculated by:

$$P_D = R_{DS(ON)} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

T_A = Ambient temperature °C

$R_{\theta JA}$ = Thermal resistance

P_D = Total power dissipation

Application Note (Continued)

Thermal Protection

Thermal protection prevents the IC from damage when heavy-overload or short-circuit faults are present for extended periods of time. The AP2162/AP2172 implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately 140°C due to excessive power dissipation in an over-current or short-circuit condition the internal thermal sense circuitry turns the power switch off, thus preventing the power switch from damage. Hysteresis is built into the thermal sense circuit allowing the device to cool down approximately 25°C before the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed. The FLG open-drain output is asserted when an over-temperature shutdown or over-current occurs with 7-ms deglitch.

Under-voltage Lockout (UVLO)

Under-voltage lockout function (UVLO) keeps the internal power switch from being turned on until the power supply has reached at least 1.9V, even if the switch is enabled. Whenever the input voltage falls below approximately 1.9V, the power switch is quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

Host/Self-Powered HUBs

Hosts and self-powered hubs (SPH) have a local power supply that powers the embedded functions and the downstream ports (see Figure 2). This power supply must provide from 5.25V to 4.75V to the board side of the downstream connection under both full-load and no-load conditions. Hosts and SPHs are required to have current-limit protection and must report over-current conditions to the USB controller. Typical SPHs are desktop PCs, monitors, printers, and stand-alone hubs.

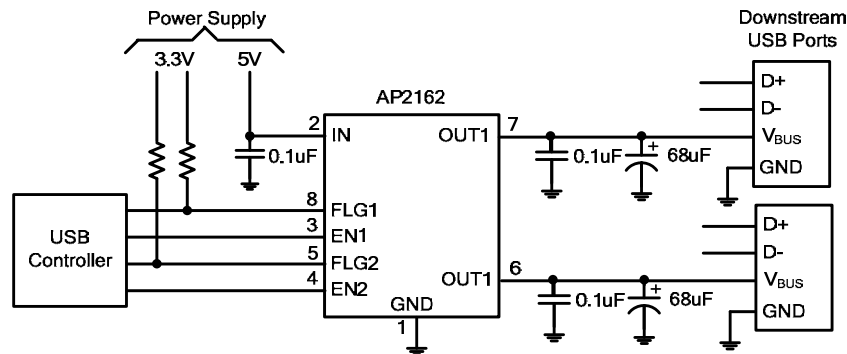


Figure 2. Typical Two-Port USB Host / Self-Powered Hub

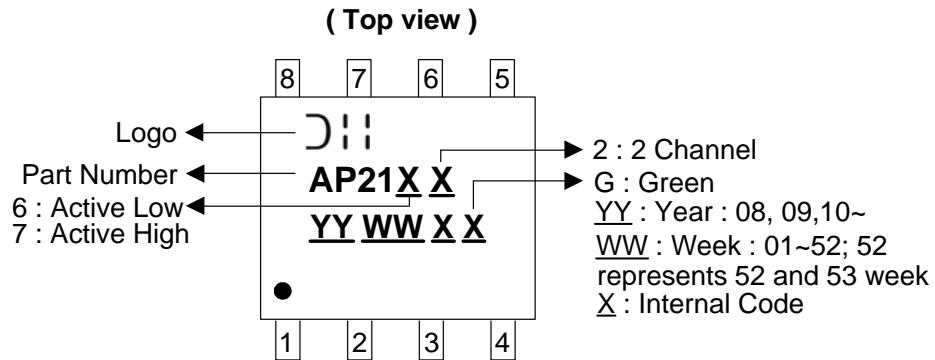
Generic Hot-Plug Applications

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the AP2162/AP2172, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the AP2162/AP2172 also ensures that the switch is off after the card has been removed, and that the switch is off during the next insertion.

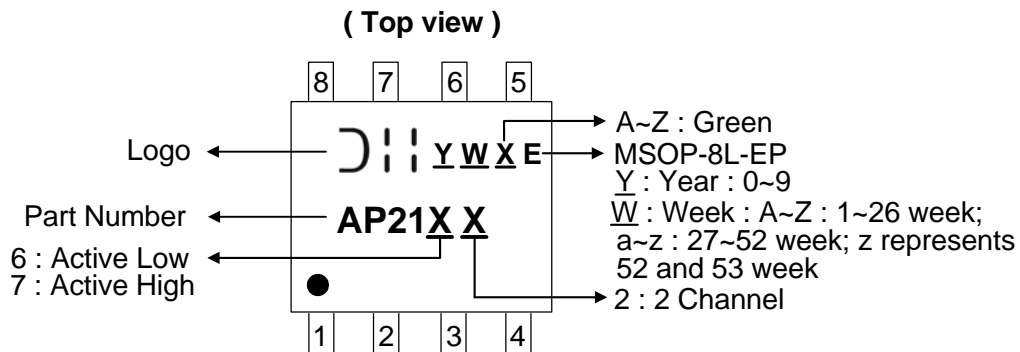
By placing the AP2162/AP2172 between the Vcc input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge current and provides a hot-plugging mechanism for any device.

Marking Information

(1) SOP-8L

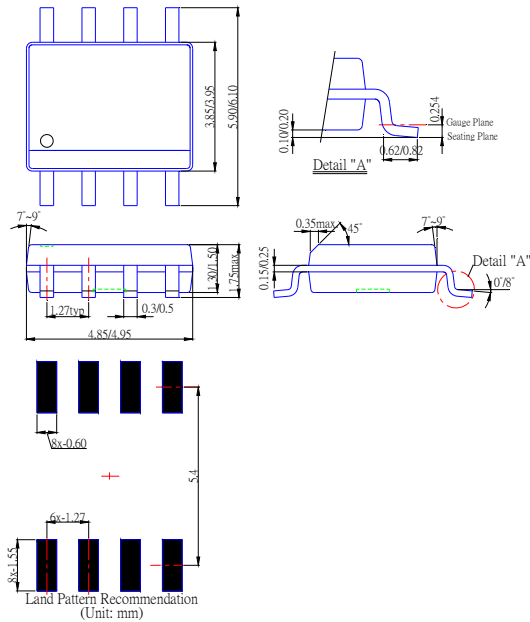


(2) MSOP-8L-EP

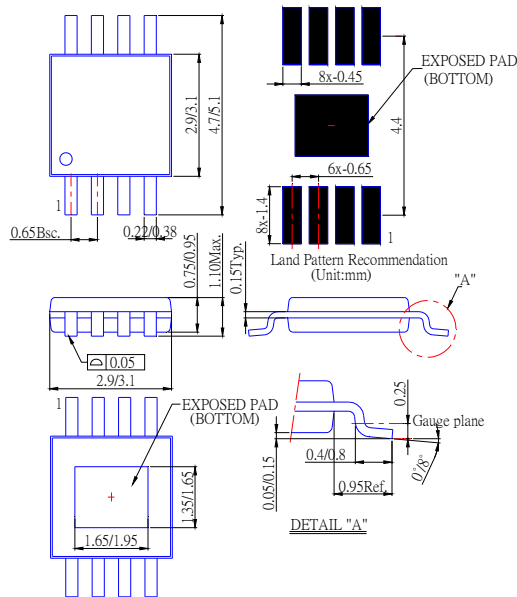


Package Information (All Dimensions in mm)

(1) Package type: SOP-8L



(2) Package type: MSOP-8L-EP





AP2162/AP2172

1A DUAL CHANNEL CURRENT-LIMITED POWER SWITCH

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